

Extremely low capacitance bidirectional ESD protection diodeRev. 1 — 1 February 2012Product data sheet

#### 1. **Product profile**

## **1.1 General description**

Extremely low capacitance bidirectional ElectroStatic Discharge (ESD) protection diode in a leadless ultra small SOD882 Surface-Mounted Device (SMD) plastic package designed to protect one signal line from the damage caused by ESD and other transients. The combination of extremely low capacitance, high ESD maximum rating and ultra small package makes the device ideal for high-speed data line protection.

## 1.2 Features and benefits

- Bidirectional ESD protection of one line ESD protection up to 15 kV
- Extremely low capacitance:  $C_{d} = 0.85 \text{ pF}$
- Low clamping voltage: V<sub>CL</sub> = 17 V
- Ultra low leakage current: I<sub>RM</sub> = 1 nA

## 1.3 Applications

- Computers and peripherals
- Audio and video equipment
- Cellular handsets and accessories
- 10/100/1000 Mbit/s Ethernet

- IEC 61000-4-2; level 4 (ESD)
- AEC-Q101 qualified
- Communication systems
- Portable electronics
- SIM card protection
- USB, High-Definition Multimedia Interface (HDMI), FireWire

#### 1.4 Quick reference data

Table 1.	Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per devi	ce					
V <sub>RWM</sub>	reverse standoff voltage		-	-	5.5	V
C <sub>d</sub>	diode capacitance	$f = 1 \text{ MHz}; V_R = 0 \text{ V}$	-	0.85	0.95	pF



#### Extremely low capacitance bidirectional ESD protection diode

# 2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	cathode (diode 1)		
2	cathode (diode 2)	1 2	1 2 sym045
		Transparent top view	

## 3. Ordering information

Table 3. Ordering	information		
Type number	Package		
	Name	Description	Version
PESD5V0X1BCAL	-	leadless ultra small plastic package; 2 terminals; body 1.0 $\times$ 0.6 $\times$ 0.5 mm	SOD882

## 4. Marking

Table 4.	Marking codes	
Type num	iber	Marking code
PESD5V0	X1BCAL	NN

## 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

			,		
Symbol	Parameter	Conditions	Min	Max	Unit
Per device					
I <sub>PPM</sub>	rated peak pulse current	t <sub>p</sub> = 8/20 μs	<u>[1]</u> -	1.8	А
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device stressed with ten non-repetitive current pulses (8/20  $\mu$ s exponential decay waveform according to IEC 61000-4-5 and IEC 61643-321).

#### Extremely low capacitance bidirectional ESD protection diode

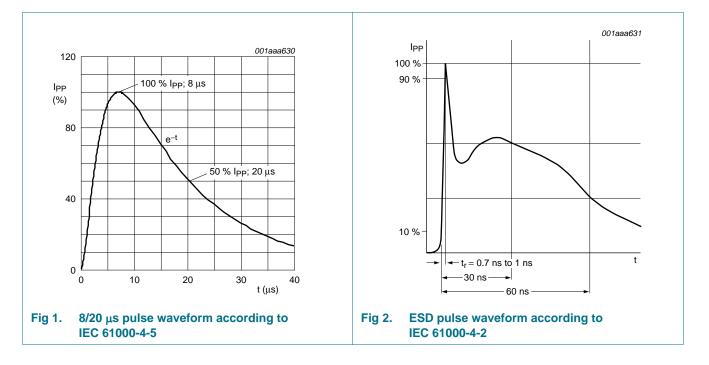
#### Table 6.ESD maximum ratings

 $T_{amb} = 25 \ ^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	N	lin Max	Unit
Per devic	e				
V <sub>ESD</sub>	electrostatic discharge voltage	IEC 61000-4-2 (air discharge)	<u>[1]</u> -	15	kV
		IEC 61000-4-2 (contact discharge)	<u>[1]</u> -	15	kV
		machine model	-	400	V
		MIL-STD-883 (human body model)	-	10	kV

[1] Device stressed with ten non-repetitive ESD pulses.

# Table 7. ESD standards complianceStandardConditionsPer deviceIEC 61000-4-2; level 4 (ESD)> 15 kV (air); > 8 kV (contact)MIL-STD-883; class 3B (human body model)> 8 kV



#### Extremely low capacitance bidirectional ESD protection diode

## 6. Characteristics

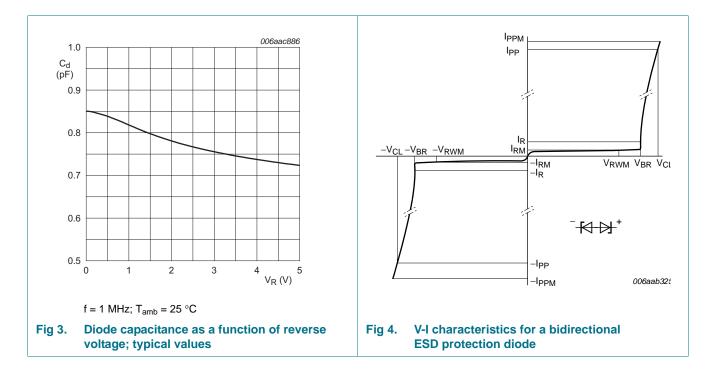
#### Table 8.Characteristics

 $T_{amb} = 25 \ ^{\circ}C$  unless otherwise specified.

$\begin{array}{c c c c c c c c } \hline \textbf{Symbol} & \textbf{Parameter} & \textbf{Conditions} & \textbf{Min} & \textbf{Typ} & \textbf{Max} & \textbf{Unit} \\ \hline \textbf{Per device} & & & & & \\ \hline \textbf{Per device} & & & & & \\ \hline \textbf{V}_{RWM} & \text{reverse standoff} & & & & & & & \\ \hline \textbf{voltage} & & & & & & & & \\ \hline \textbf{I}_{RM} & \text{reverse leakage current} & V_{RWM} = 5.5 \ V & & - & & <1 & 10 & nA \\ \hline \textbf{V}_{BR} & \text{breakdown voltage} & \textbf{I}_{R} = 10 \ \text{mA} & 8.1 & 9.8 & 12.3 & V \\ \hline \textbf{C}_{d} & \text{diode capacitance} & \textbf{f} = 1 \ \text{MHz}; \ \textbf{V}_{R} = 0 \ V & - & 0.85 & 0.95 & \text{pF} \\ \hline \textbf{V}_{CL} & \text{clamping voltage} & \textbf{I}_{PPM} = 1.8 \ A & \ \textbf{11} & - & - & 17 & V \\ \hline \textbf{r}_{dyn} & \text{dynamic resistance} & \textbf{I}_{R} = 10 \ A & \ \textbf{21} & - & 0.5 & - & \Omega \end{array}$	amb – 20	o unicos ouncivise spe	cilica.				
$V_{RWM}$ reverse standoff voltage5.5V $I_{RM}$ reverse leakage current $V_{RWM} = 5.5$ V-<110nA $V_{BR}$ breakdown voltage $I_R = 10$ mA8.19.812.3V $C_d$ diode capacitance $f = 1$ MHz; $V_R = 0$ V-0.850.95pF $V_{CL}$ clamping voltage $I_{PPM} = 1.8$ A[1]17V	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
voltage $I_{RM}$ reverse leakage current $V_{RWM} = 5.5 \text{ V}$ -<110nA $V_{BR}$ breakdown voltage $I_R = 10 \text{ mA}$ 8.19.812.3V $C_d$ diode capacitancef = 1 MHz; $V_R = 0 \text{ V}$ -0.850.95pF $V_{CL}$ clamping voltage $I_{PPM} = 1.8 \text{ A}$ [1]-17V	Per devi	ce					
$V_{BR}$ breakdown voltage $I_R = 10 \text{ mA}$ 8.19.812.3V $C_d$ diode capacitance $f = 1 \text{ MHz}; V_R = 0 \text{ V}$ -0.850.95pF $V_{CL}$ clamping voltage $I_{PPM} = 1.8 \text{ A}$ $\begin{bmatrix} 11 \\ 2 \end{bmatrix}$ -17V	$V_{RWM}$			-	-	5.5	V
$C_d$ diode capacitancef = 1 MHz; $V_R = 0 V$ -0.850.95pF $V_{CL}$ clamping voltage $I_{PPM} = 1.8 A$ [1]-17V	I <sub>RM</sub>	reverse leakage current	$V_{RWM} = 5.5 V$	-	<1	10	nA
$V_{CL}$ clamping voltage $I_{PPM} = 1.8 \text{ A}$ [1] 17 V	$V_{BR}$	breakdown voltage	I <sub>R</sub> = 10 mA	8.1	9.8	12.3	V
	C <sub>d</sub>	diode capacitance	$f = 1 MHz; V_R = 0 V$	-	0.85	0.95	pF
$r_{dyn}$ dynamic resistance $I_R = 10 A$ [2] - 0.5 - $\Omega$	V <sub>CL</sub>	clamping voltage	I <sub>PPM</sub> = 1.8 A	<u>[1]</u> _	-	17	V
	r <sub>dyn</sub>	dynamic resistance	I <sub>R</sub> = 10 A	[2] _	0.5	-	Ω

[1] Device stressed with 8/20  $\mu$ s exponential decay waveform according to IEC 61000-4-5 and IEC 61643-321.

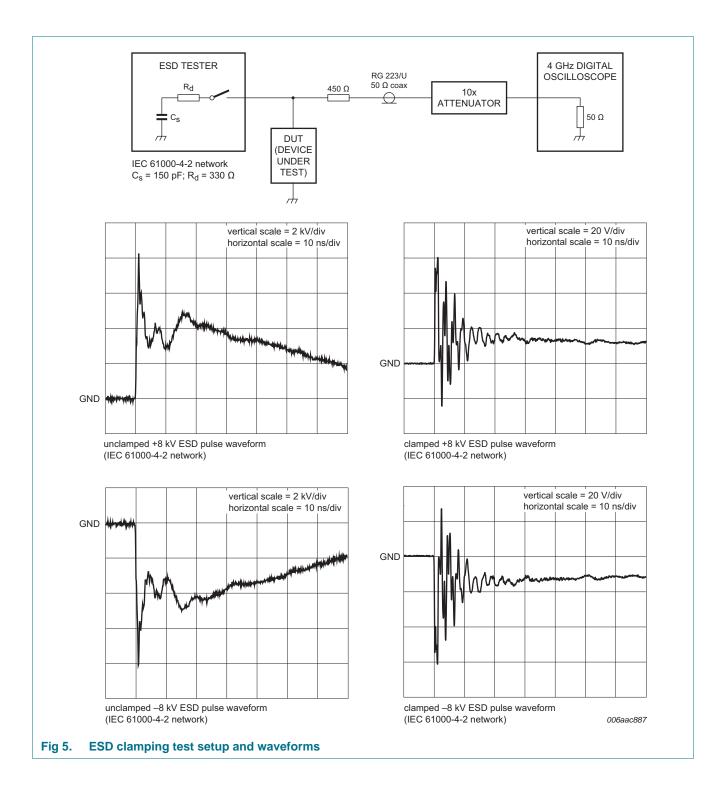
[2] Non-repetitive current pulse, Transmission Line Pulse (TLP)  $t_p$  = 100 ns; square pulse; ANS/IESD STM5-1-2008.



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# PESD5V0X1BCAL

#### Extremely low capacitance bidirectional ESD protection diode

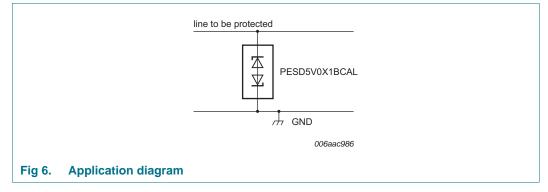


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#### Extremely low capacitance bidirectional ESD protection diode

# 7. Application information

PESD5V0X1BCAL is designed for the protection of one bidirectional data or signal line from surge pulses and ESD damage. The device is suitable on lines where the signal polarities are both, positive and negative with respect to ground.



#### Circuit board layout and protection device placement

Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

- 1. Place the device as close to the input terminal or connector as possible.
- 2. Minimize the path length between the device and the protected line.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protected conductors in parallel with unprotected conductors.
- 5. Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- 8. Use ground planes whenever possible. For multilayer PCBs, use ground vias.

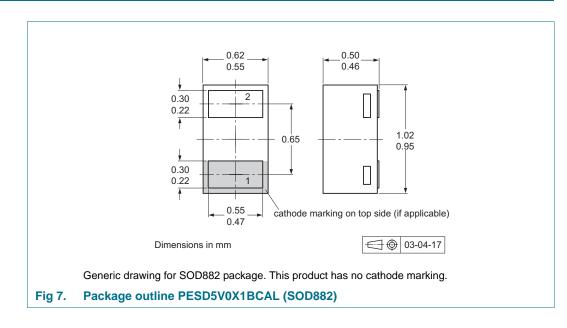
## 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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## 9. Package outline



# **10. Packing information**

#### Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

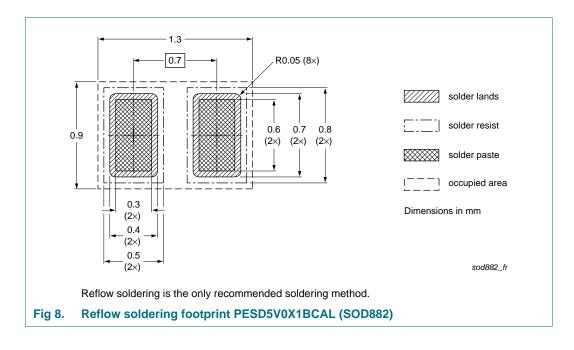
Type number	Package	Description	Packing quantity
			10000
PESD5V0X1BCAL	SOD882	2 mm pitch, 8 mm tape and reel	-315

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

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# 11. Soldering



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# **12. Revision history**

Table 10. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PESD5V0X1BCAL v.1	20120201	Product data sheet	-	-	

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# 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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